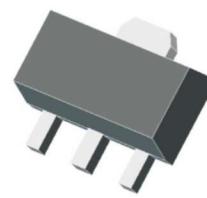


# CMS0103M-HF

**N-Channel  
RoHS Device  
Halogen Free**



## Features

- $V_{DS} = 100V, I_D = 3A$
- $R_{DS(ON)} < 160m\Omega @ V_{GS}=10V$  (Typ:136m  $\Omega$ )
- $R_{DS(ON)} < 170m\Omega @ V_{GS}=4.5V$  (Typ:140m  $\Omega$ )
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

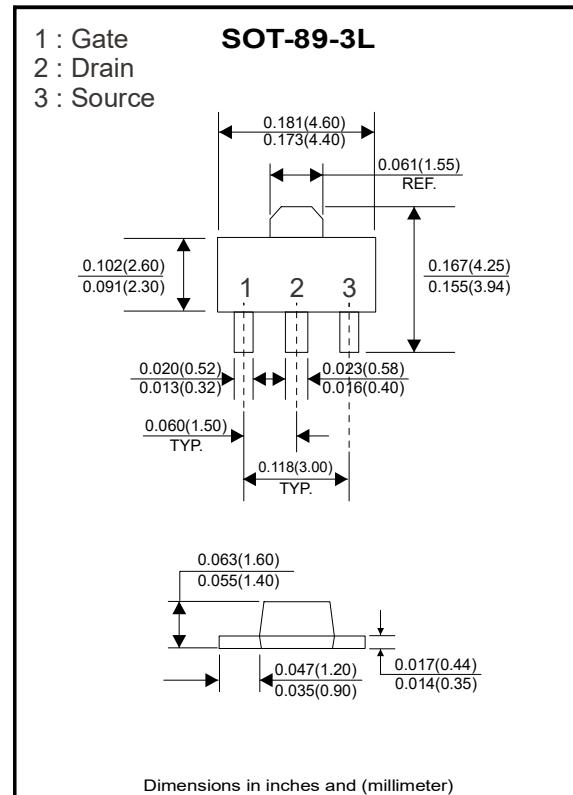
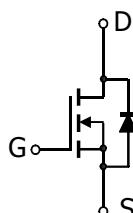
## Description

The CMS3404 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for use as a load switch and PWM applications.

## Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

## Circuit Diagram



## Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	3	A
Drain Current-Pulsed <sup>(Note 1)</sup>	$I_{DM}$	20	A
Maximum Power Dissipation	$P_D$	1.5	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

## Thermal Characteristic

Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	83	°C/W
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## Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	100	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b> <sup>(Note 3)</sup>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.8	1.1	2.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =3A	-	136	160	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A	-	140	170	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =3A	-	5	-	S
<b>Dynamic Characteristics</b> <sup>(Note 4)</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, F=1.0MHz	-	650	-	PF
Output Capacitance	C <sub>oss</sub>		-	24	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	20	-	PF
<b>Switching Characteristics</b> <sup>(Note 4)</sup>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =50V, R <sub>L</sub> =19Ω V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω	-	6	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	4	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	20	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	4	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =50V, I <sub>D</sub> =3A, V <sub>GS</sub> =10V	-	20	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	2.1	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	3.3	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =3A	-	-	1.2	V
Diode Forward Current <sup>(Note 2)</sup>	I <sub>S</sub>		-	-	3	A

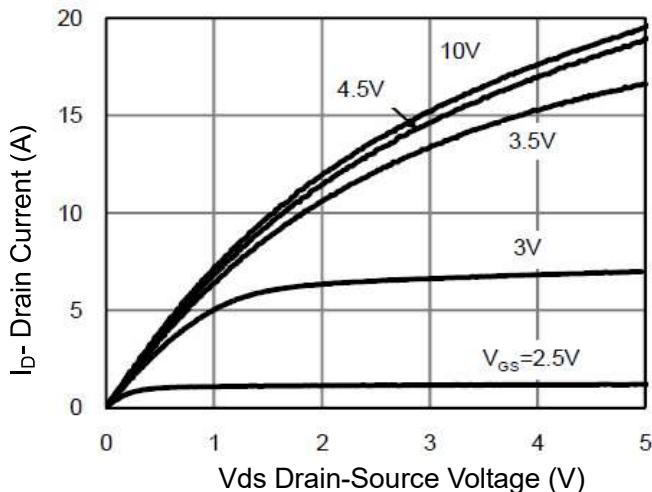
### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to productio

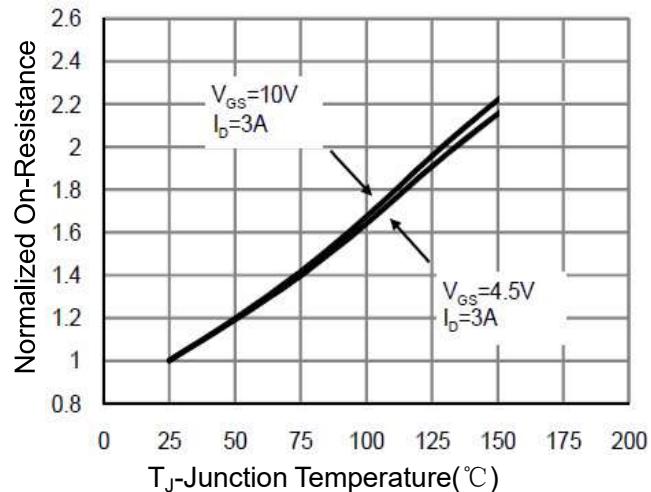
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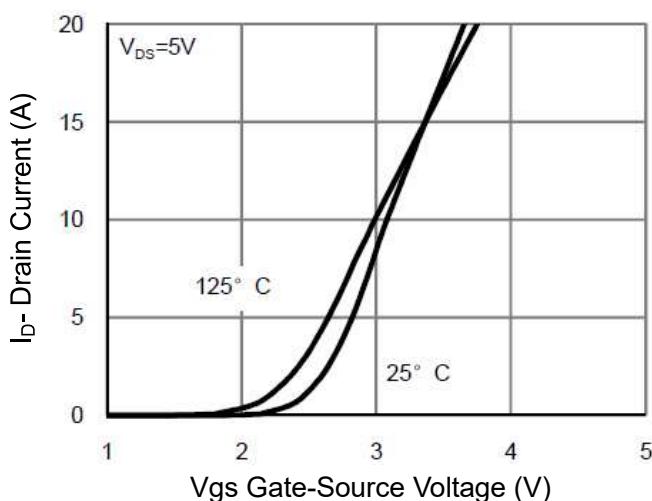
## Typical Electrical and Thermal Characteristics (Curves)



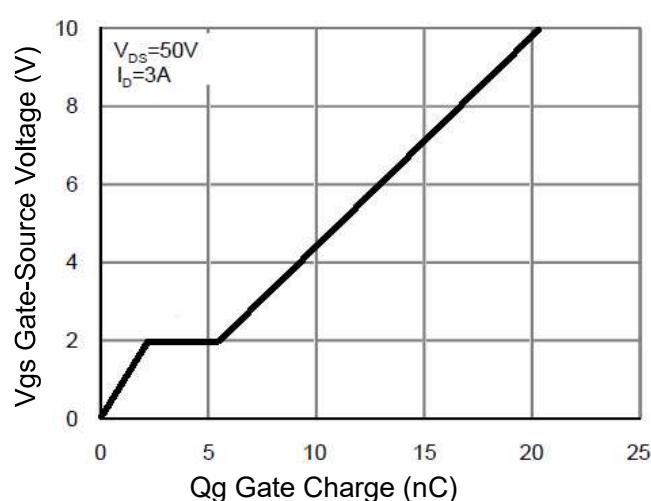
**Figure 1 Output Characteristics**



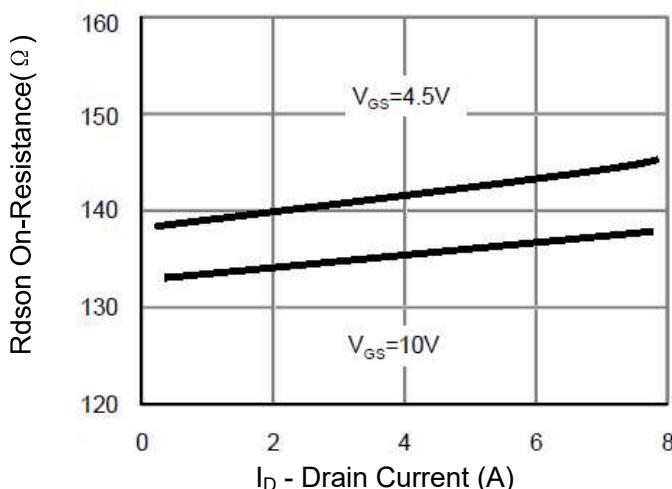
**Figure 4 Rdson-JunctionTemperature**



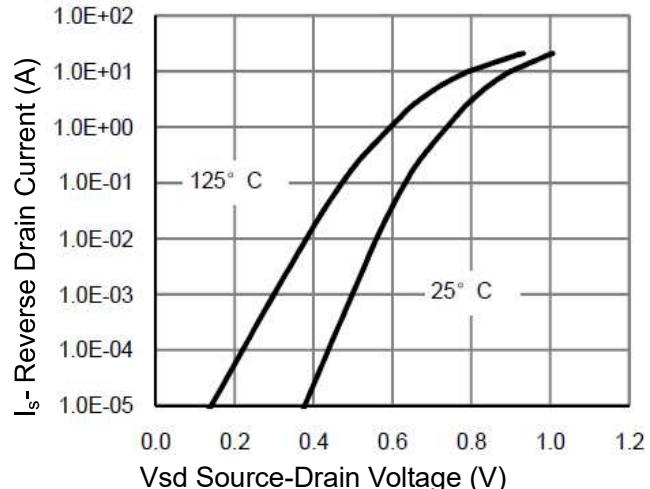
**Figure 2 Transfer Characteristics**



**Figure 5 Gate Charge**



**Figure 3 Rdson- Drain Current**



**Figure 6 Source- Drift Diode Forward**

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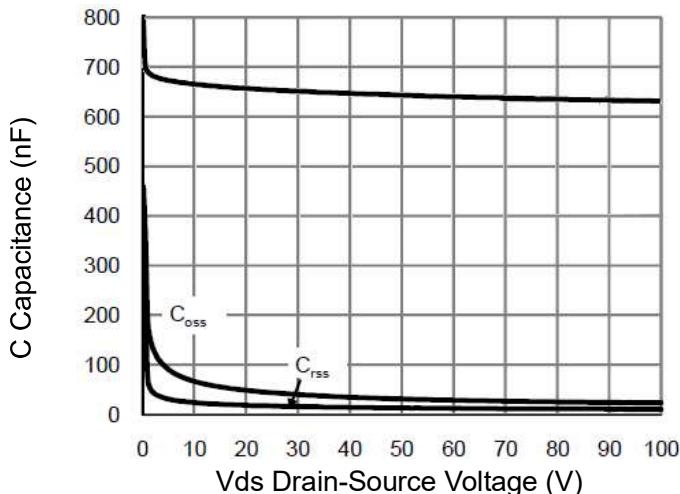


Figure 7 Capacitance vs Vds

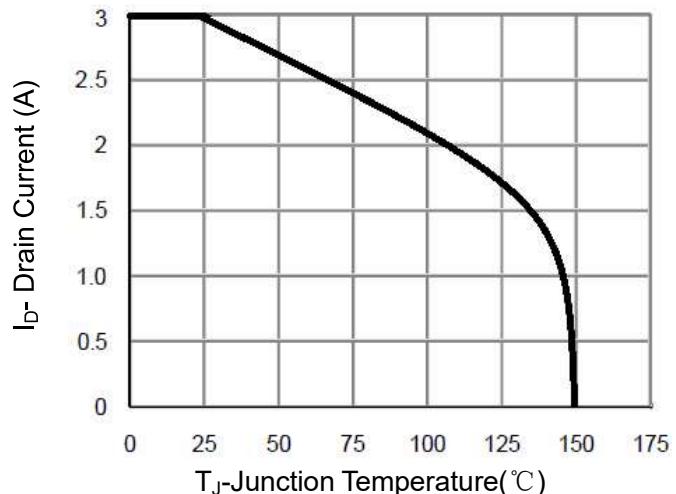


Figure 9  $BV_{DSS}$  vs Junction Temperature

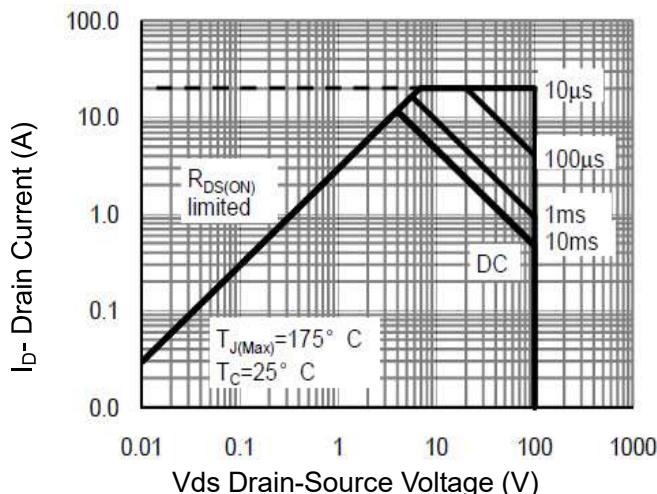


Figure 8 Safe Operation Area

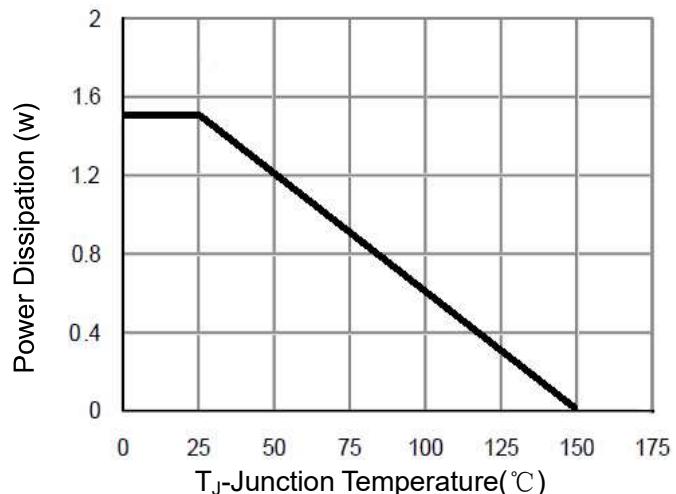


Figure 10 Power De-rating

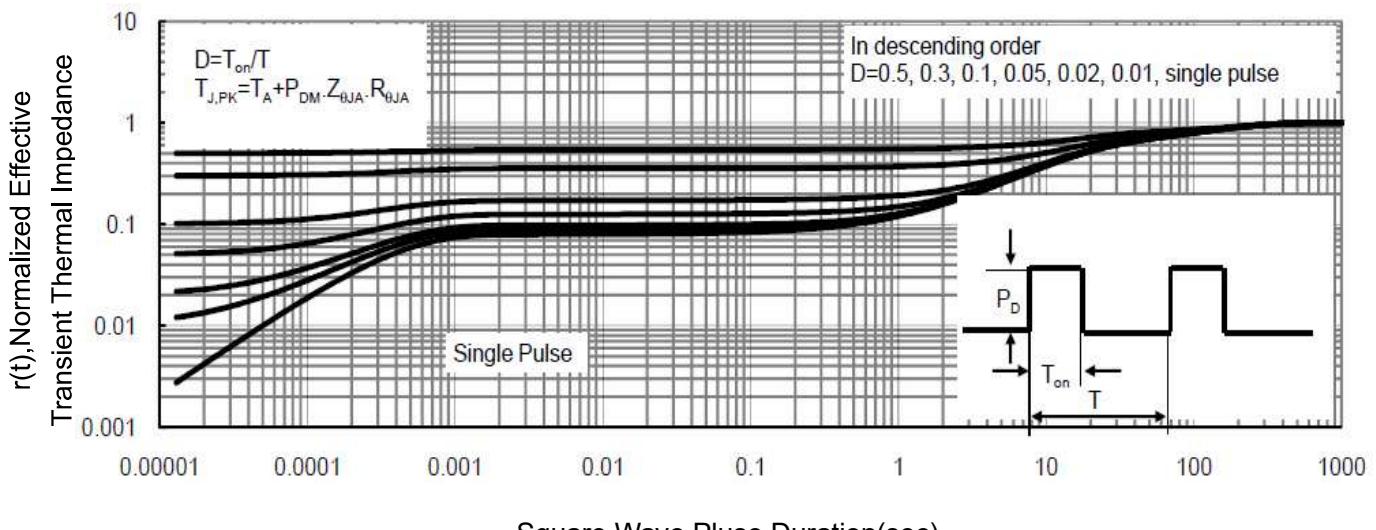
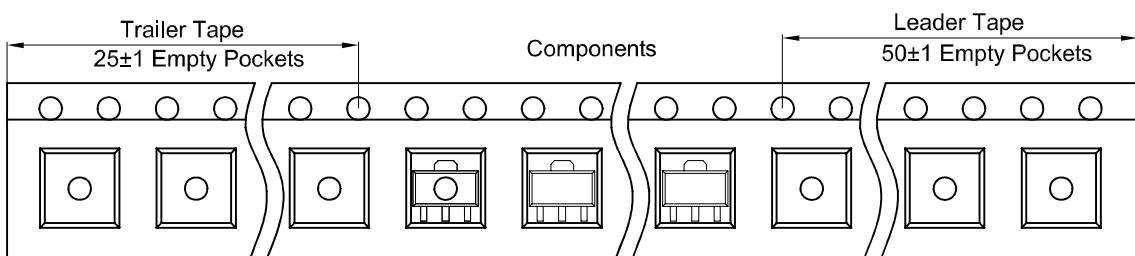
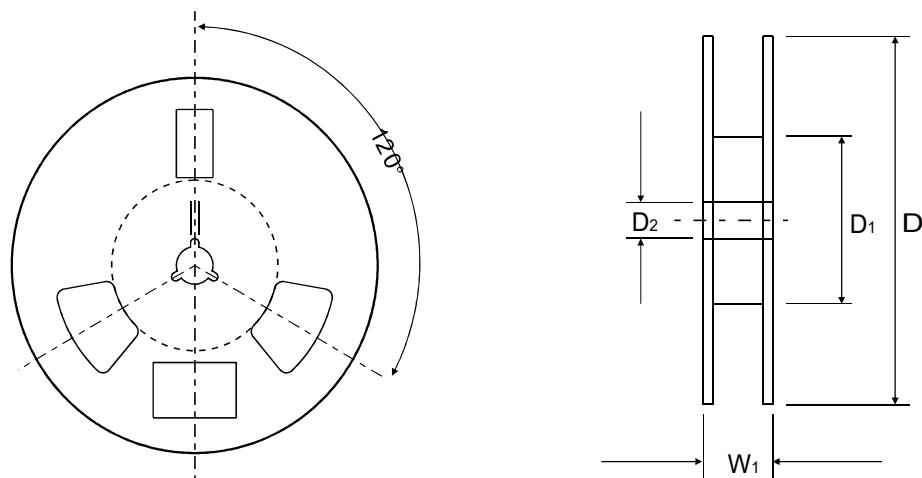
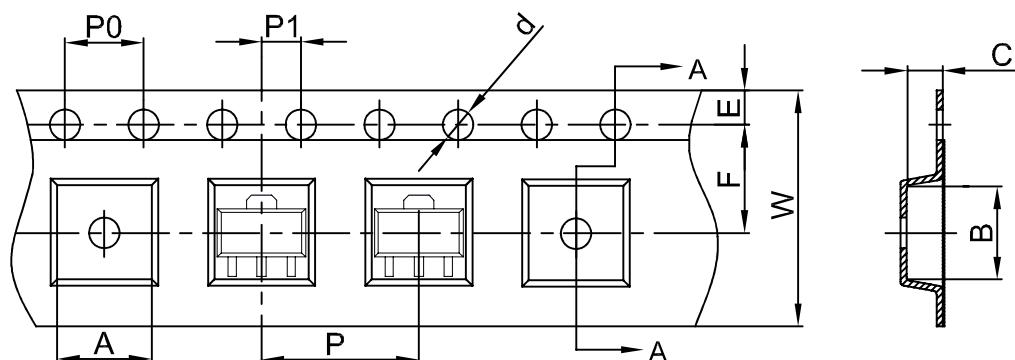


Figure 11 Normalized Maximum Transient Thermal Impedance

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## Reel Taping Specification



	SYMBOL	A	B	C	d	D	D1	D2
SOT-89-3L	(mm)	$4.85 \pm 0.10$	$4.45 \pm 0.10$	$1.85 \pm 0.10$	$1.50 \pm 0.10$	$180 \pm 2.00$	$60.00 \pm 1.00$	$R32.00 \pm 1.00$
	(inch)	$0.191 \pm 0.004$	$0.175 \pm 0.004$	$0.073 \pm 0.004$	$0.059 \pm 0.004$	$7.087 \pm 0.079$	$2.362 \pm 0.039$	$1.260 \pm 0.039$

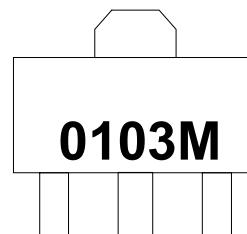
	SYMBOL	E	F	P	$P_0$	$P_1$	W	$W_1$
SOT-89-3L	(mm)	$1.75 \pm 0.10$	$5.50 \pm 0.10$	$8.00 \pm 0.10$	$4.00 \pm 0.10$	$2.00 \pm 0.10$	$12.00 \pm 0.30 / -0.10$	$16.50 \pm 1.00$
	(inch)	$0.069 \pm 0.004$	$0.217 \pm 0.004$	$0.315 \pm 0.004$	$0.158 \pm 0.004$	$0.079 \pm 0.004$	$0.472 \pm 0.012 / -0.004$	$0.650 \pm 0.039$

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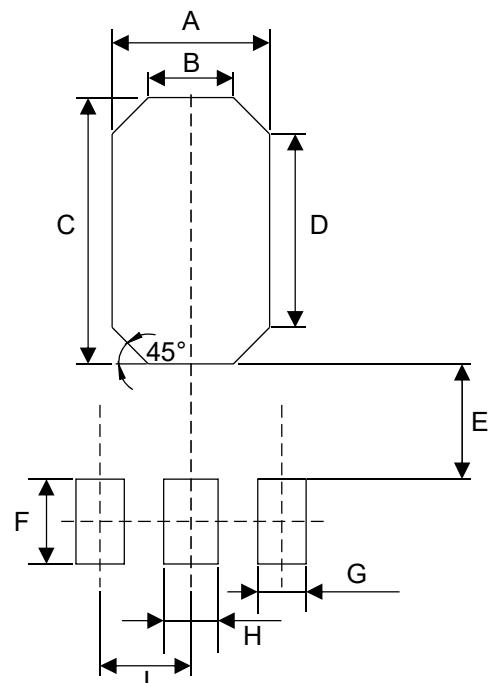
## Marking Code

Part Number	Marking Code
CMS0103M-HF	0103M



## Suggested PAD Layout

SIZE	SOT-89-3L	
	(mm)	(inch)
A	2.60	0.102
B	1.40	0.055
C	4.40	0.173
D	3.20	0.126
E	1.90	0.075
F	1.40	0.055
G	0.80	0.032
H	0.90	0.035
I	1.50	0.059



## Standard Packaging

Case Type	REEL PACK	
	REEL ( pcs )	Reel Size (inch)
SOT-89-3L	1,000	7

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